

isc Silicon NPN Power Transistor

2SC4461

DESCRIPTION

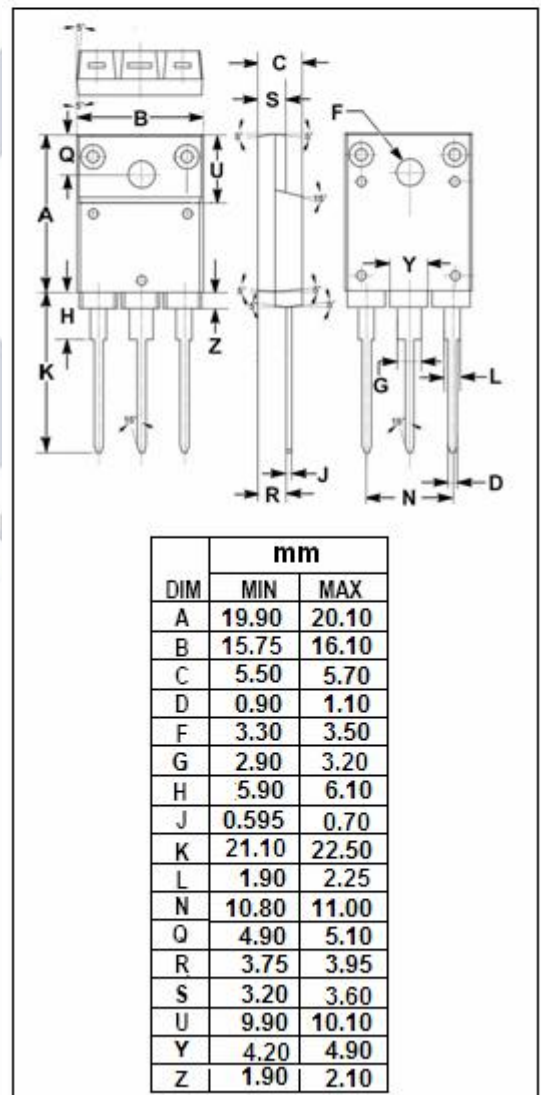
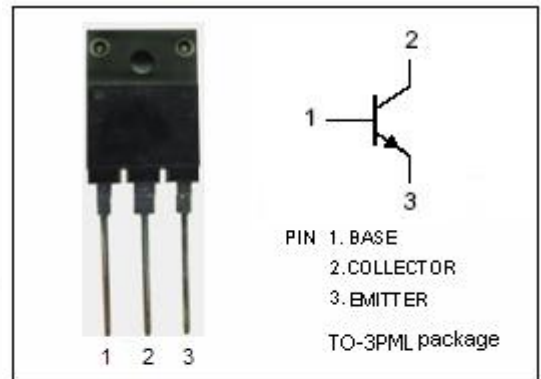
- High Breakdown Voltage-  
:  $V_{(BR)CEO} = 500V(\text{Min})$
- Fast Switching speed
- Wide Area of Safe Operation

APPLICATIONS

- Designed for switching regulator applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	500	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	25	A
$I_{CP}$	Collector Current-Pulse	40	A
$I_B$	Base Current-Continuous	8	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	65	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3	
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SC4461****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; R_{BE}=\infty$	500			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=12\text{A}; I_B=2.4\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=12\text{A}; I_B=2.4\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=2.4\text{A}; V_{CE}=5\text{V}$	15		50	
$h_{FE-2}$	DC Current Gain	$I_C=12\text{A}; V_{CE}=5\text{V}$	8			
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		260		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=2.4\text{A}; V_{CE}=10\text{V}$		18		MHz

◆  **$h_{FE-1}$  Classifications**

L	M	N
15-30	20-40	30-50